

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	48	(FET or transistor) same ("gate oxide" or FOx) same (etch adj stop\$4) same ("contact hole" or SAC or (self adj align\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:18			
2	BRS	L2	68	(FET or transistor) same ("gate oxide") same (etch adj stop\$4) same ((contact adj (hole or opening)) or SAC or (self adj align\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:01			
3	BRS	L3	3226	(FET or transistor) same ("gate oxide") same ((contact adj (hole or opening)) or SAC or (self adj align\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 15:29			
4	BRS	L4	1392	3 same etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:20			
5	BRS	L5	1196	4 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 15:58			
6	BRS	L6	1405	3 same (wet etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:20			
7	BRS	L7	2721	3 and (wet etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:57			
8	BRS	L8	177	7 and (HF or hydrofluoric) and (phosphoric or "H.sub.3PO.sub.4" or H3PO4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:59			
9	BRS	L9	153	8 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:22			
10	BRS	L10	1415	3 and (wet etch\$3) and ((dry or plasma or rie or "reactive ion") adj etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/17 14:58			